

Amendments to the Specification:

Please remove Table 1, Table 2, Table 3, and Table 4 from the disclosure.

Please amend paragraph [0007] as shown:

[0007] The graph shown in Figure 4 below presents the results of experiments comparing the particle removal rates of the current cleaning with SC-1 and cleaning with hydrogen water, for wafers with a silicon oxide film and bare-silicon wafers. What were compared were hydrogen with hydrogen water (in-solution hydrogen concentration: 0.6 ppm) (example 1), hydrogen water to which 1 ppm of ammonia (NH₄OH) is added (example 2), SC-1 heated to 40°C (example 3), and SC-2 heated to 80°C (example 4). Also, except in the case of example 4, ultrasonic vibration is applied during the cleaning.

Please add the following to the "Brief Description of Drawings" section of the disclosure:

Figure 4 Results of experiments comparing the particle removal rates of various cleaning agents on silicon oxide film wafers and bare-silicon wafers.

Figure 5 Results of experiments according to an embodiment of the instant invention.

Figure 6 Relationship between hydrogen concentration and particle removal rate (ammonia mixed into the hydrogen water).

Figure 7 Relationship between hydrogen water concentration and particle removal rate (ammonia not mixed into hydrogen water).

Please amend paragraph [0035] as shown:

[0034] Also, in each cleaning process, cleaning solution was supplied into an 18.24-liter cleaning tank at a supply quantity of 15.0 liter/min, and the solution wafers were immersed for 10 minutes in each tank. If ultrasonic waves were used, their output was set to 1.0 MHz, 4.1 W/cm². Measurement of the residual particles was applied to those of size 0.2 um or larger, using a laser diffusion type particle counter. The results are shown in Figure 5 ~~the following graph~~.

Please amend paragraph [0039] as shown:

[0039] In the experiments, samples were made in which about 300-400 particles per 6 inches were intentionally made to adhere onto bare-silicon wafers and silicon oxide film wafers, they were cleaned using hydrogen water of varying in-solution hydrogen water concentrations, and the number of particles remaining after cleaning was measured. The in-solution hydrogen of the hydrogen water was varied between 0 and 1.5 ppm. Also, in each cleaning process, hydrogen water was supplied into an 18.24-liter cleaning tank at a supply quantity of 15.0 liter/min, and the silicon wafers were immersed for 10 minutes in each tank. The ultrasonic wave output was set to 1.0 MHz, 4.1 W/cm². Measurement of the residual particles was applied to those of size 0.2 um or larger, using a laser diffusion type particle counter. The experiments were carried out on hydrogen water into which 1 ppm (pH = 9.4) ammonia was mixed (Figure 6~~Table 3~~) and on hydrogen water into which none was mixed (Figure 7~~Table 4~~). The results are shown in Figure 6 and Figure 7 ~~the following graph~~.